

Serial No. 09/755,164
Docket No. YOR920000642US1

2

AMENDMENTS TO THE CLAIMS:

1. (Currently amended) A field effect transistor, comprising:

a substrate comprising a source region, a drain region, and a channel region between said source region and said drain region;

an insulating layer disposed over said channel region, said insulating layer comprising an aluminum nitride a layer comprising ~~aluminum nitride~~ and at least one of a ~~layer of an~~ aluminum oxide layer, a ~~layer of~~ silicon dioxide layer, and a ~~layer of~~ silicon nitride layer disposed over said channel region; and

a gate electrode disposed over said insulating layer.
2. (Currently amended) The transistor of claim 1, wherein said insulating layer comprises an of aluminum oxide layer is disposed upon said channel region, and wherein said ~~layer of~~ aluminum nitride layer is disposed over said aluminum oxide layer.
3. (Currently amended) The transistor of claim 1, wherein said insulating layer comprises an of aluminum oxide layer is disposed over said channel region, and wherein said ~~layer of~~ aluminum nitride layer is disposed under said aluminum oxide layer.
4. (Currently amended) The transistor of claim 1, wherein said insulating layer comprises a of silicon dioxide layer is disposed upon said channel region, and wherein said ~~layer of~~ aluminum nitride layer is disposed over said silicon dioxide layer.

Serial No. 09/755,164
Docket No. YOR920000642US1

3

5. (Currently amended) The transistor of claim 1, wherein said insulating layer comprises a of silicon dioxide layer is disposed over said channel region, and wherein said ~~layer of~~ aluminum nitride layer is disposed under said silicon dioxide layer.

6. (Currently amended) The transistor of claim 1, wherein said insulating layer comprises a of silicon nitride layer is disposed upon said channel region, and wherein said ~~layer of~~ aluminum nitride layer is disposed over said silicon nitride layer.

7. (Currently amended) The transistor of claim 1, wherein said insulating layer comprises a of silicon nitride layer is disposed over said channel region, and wherein said ~~layer of~~ aluminum nitride layer is disposed under said silicon nitride layer.

Claims 8-13. (Canceled)

14. (Currently amended) A field effect transistor, comprising:
a substrate comprising a source region, a drain region, and a channel region between said source region and said drain region;
an insulating layer disposed over said channel region, said insulating layer comprising an ~~a first layer comprising~~ aluminum oxide layer disposed upon said channel region and an ~~a second layer comprising~~ aluminum nitride layer disposed upon said aluminum oxide first layer; and

Serial No. 09/755,164
Docket No. YOR920000642US1

4

a gate electrode disposed over said insulating layer.

15. (Currently amended) A semiconductor device, comprising:

a substrate comprising a source region, a drain region, and a channel region between said source region and said channel region;

an insulating layer disposed over said channel region, said insulating layer comprising an ~~a layer comprising~~ aluminum nitride layer and ~~a layer comprising~~ at least one of an aluminum oxide layer, a silicon dioxide layer, and a silicon nitride layer; and

a gate electrode disposed over said insulating layer.

16. (Original) The semiconductor device of claim 15, wherein said device comprises a field effect transistor.

17. (Currently amended) A multi-terminal device, comprising:

a substrate comprising a source region, a drain region, and a channel region between said source region and said channel region;

an insulating layer disposed over said channel region, said insulating layer comprising an aluminum nitride layer and ~~a layer comprising~~ at least one of an aluminum oxide layer, a silicon dioxide layer, and a silicon nitride layer; and

a gate electrode disposed over said insulating layer.

Serial No. 09/755,164
Docket No. YOR920000642US1

5

18. (Original) The multi-terminal device of claim 17, wherein said device comprises a field effect transistor.

Claims 19-27. (Canceled)